

View Online at <https://aerobasegroup.com/nsn/5961-01-579-5547>

Inclosure Material:

Plastic

Overall Length:

1.550 inches

Overall Height:

0.815 inches

Overall Width:

1.050 inches

Function For Which Designed:

General purpose

End Application:

Ef2000 aircraft

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Internal Junction Configuration:

Pnp

Mounting Method:

Unthreaded hole

Features Provided:

High power

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

120.0 collector-to-emitter, substaining voltage, base open-circuited

Current Rating Per Characteristic:

15.00 amperes collector current, dc

Power Rating Per Characteristic:

180.0 watts off-state power dissipation

Transfer Ratio:

5.0 static forward current transfer ratio, common-emitter and 70.0 static forward current transfer ratio, common-emitter

Maximum Operating Temperature Per Measurement Point:

200.0 degrees celsius junction

Product Name:

Discrete pnp transistor

Special Features:

Type to-20 (to-3) ; container type-tray; quanti type 100; designed for high power audio, stepping motor and linear applications; used in power switching circuits-relays or solenoid drivers, dc to dc converters, inverters or inductive load

Special Test Features:

Pb-free

Terminal Type And Quantity:

2 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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